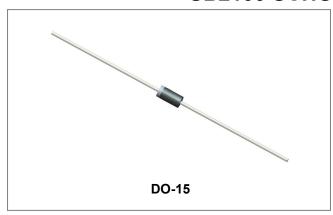






SB2100 SCHOTTKY RECTIFIER



Features

- Schottky Barrier Chip
- Ideally Suited for Automatic Assembly
- Low Power Loss, High Efficiency
- Surge Overload Rating to 50A Peak
- For Use in Low Voltage Application
- **Guard Ring Die Construction**
- Plastic Case Material has UL Flammability
- Classification Rating 94V-O
- Green Products in Compliance with the RoHS Directive
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Applications

- · Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Disk drives

Maximum Ratings

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$egin{array}{c} V_{RRM} \ V_{RWM} \ V_{R} \end{array}$	-	100	V
Average Rectified Forward Current	I _{F (AV)}	50% duty cycle @T _C =100°C rectangular wave form(L=0.375")	2.0	Α
Peak One Cycle Non-Repetitive Surge Current	I _{FSM}	8.3 ms, half Sine pulse, T _J = 25℃	50	Α

Electrical Characteristics

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	V_{F1}	@ 2.0A, Pulse, T _J = 25℃	0.70	0.85	V
Reverse Current*	I _{R1}	$@V_R = \text{rated } V_R$ $T_J = 25 ^{\circ} C$	0.02	0.5	mA
	I _{R2}	$@V_R = \text{rated } V_R$ $T_J = 100^{\circ}C$	10	20	mA
Junction Capacitance	Сл	$@V_R = 5V, T_C = 25 °C$ $f_{SIG} = 1MHz$	120	140	pF

^{*} Pulse width < 300 µs, duty cycle < 2%



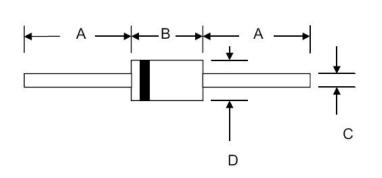




Thermal-Mechanical Specifications

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T_J	-	-55 to +150	°C
Storage Temperature	T _{stg}	-	-55 to +150	°C
Typical Thermal Resistance Junction to Case	R _θ Jc	DC operation	8	°C/W
Approximate Weight	wt	-	0.093	g

Mechanical Dimensions DO-15



SYMBOL	Millin	neters	Inches		
O'IMBOL	Min.	Max.	Min.	Max.	
А	25.4	-	1.000	-	
В	5.5	7.62	0.217	0.300	
С	0.6	0.9	0.023	0.034	
D	2.6	3.6	0.104	0.140	

Ordering Information

Device	Package	Shipping
SB2100	DO-15 (Pb-Free)	3000pcs /tape

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Marking Diagram

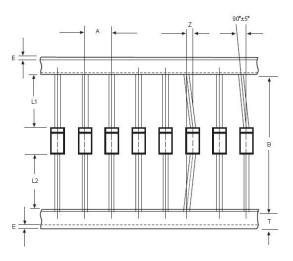
SB = Device Type 8× 2 = Forward Current (2A)

100 = Reverse Voltage (100V)
SSG = SSG
YY = Year
WW = Week
L = Lot Number

Where XXXXX is YYWWL



Carrier Tape Specification DO-15



SYMBOL	Millimeters		
	Min.	Max.	
А	4.50	5.50	
В	50.9	53.9	
Z	-	1.20	
Т	5.60	6.40	
E	-	0.80	
IL1-L2I	-	1.0	

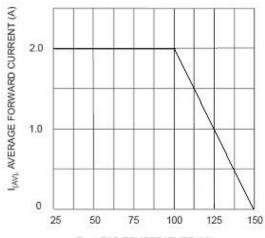
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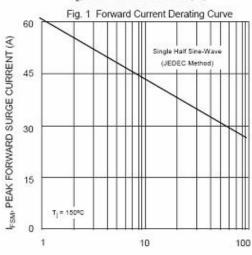




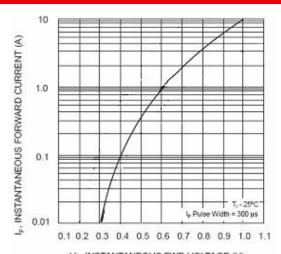
Ratings and Characteristics Curves



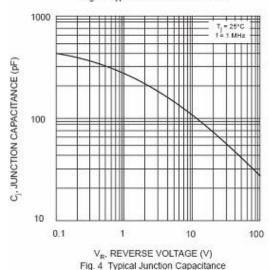
T_L, LEAD TEMPERATURE (°C)

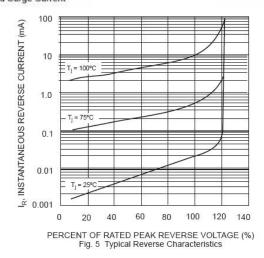


NUMBER OF CYCLES AT 60 Hz Fig. 3 Max Non-Repetitive Peak Fwd Surge Current



V_F, INSTANTANEOUS FWD VOLTAGE (V) Fig. 2 Typ. Forward Characteristics





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